

**SANYO**

No.1627B

**2SC3643**

NPN Triple Diffused Planar Silicon Transistor  
**VERY HIGH-DEFINITION DISPLAY**  
**HORIZONTAL DEFLECTION OUTPUT APPLICATIONS**

**Features**

- . High reliability (Adoption of HVP process)
- . Fast speed.
- . High breakdown voltage.
- . Adoption of MBIT process.

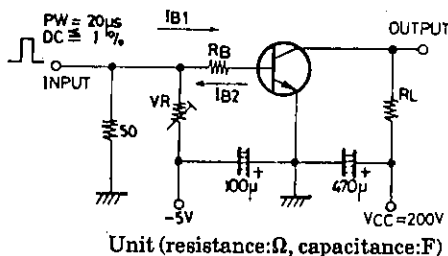
**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector-to-Base Voltage	V <sub>CB0</sub>	1200	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>	800	V
Emitter-to-Base Voltage	V <sub>EBO</sub>	7	V
Collector Current	I <sub>C</sub>	8	A
Peak Collector Current	i <sub>cp</sub>	16	A
Collector Dissipation	P <sub>C</sub>	140	W
Junction Temperature	T <sub>J</sub>	150	°C
Storage Temperature	T <sub>stg</sub>	-55 to +150	°C

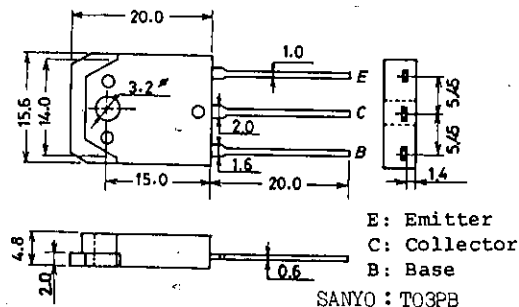
**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	I <sub>CB0</sub>	V <sub>CB</sub> =800V, I <sub>E</sub> =0			10	µA
Collector-to-Emitter Sustain Voltage	I <sub>CES</sub> V <sub>CEO(sus)</sub>	V <sub>CE</sub> =1200V, R <sub>BE</sub> =0 I <sub>C</sub> =100mA, I <sub>B</sub> =0	800		0.5	V
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			1	mA
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			5	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =6A, I <sub>B</sub> =1.2A			1.5	V
DC Current Gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1.2A	8			
Storage Time	t <sub>stg</sub>	I <sub>C</sub> =6A, I <sub>B1</sub> =1.2A, I <sub>B2</sub> =-2.4A			3.0	µs
Fall Time	t <sub>f</sub>	I <sub>C</sub> =6A, I <sub>B1</sub> =1.2A, I <sub>B2</sub> =-2.4A		0.1	0.2	µs

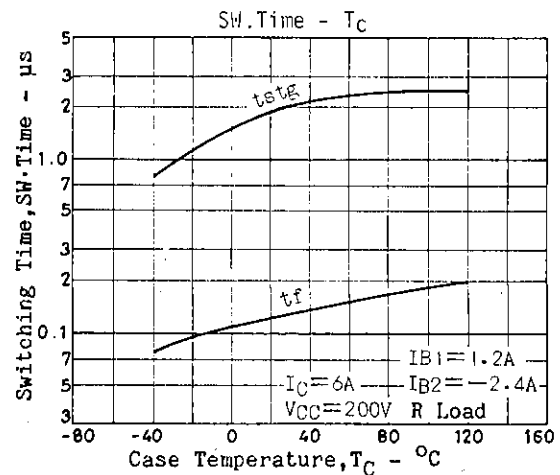
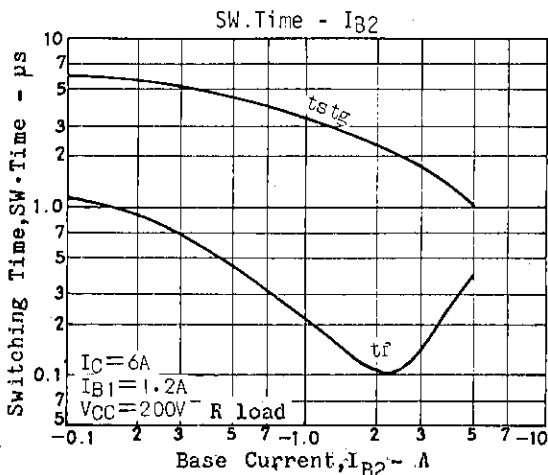
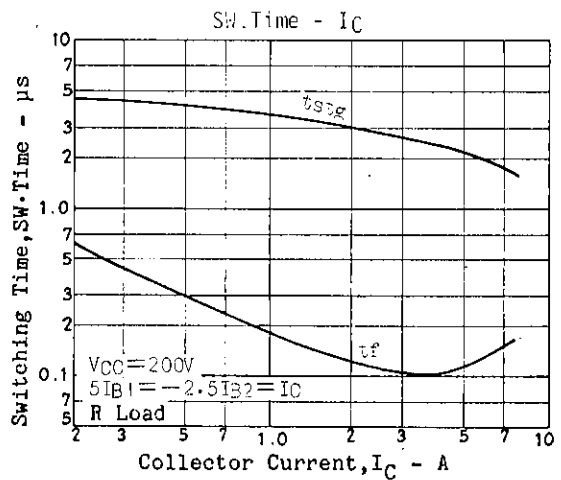
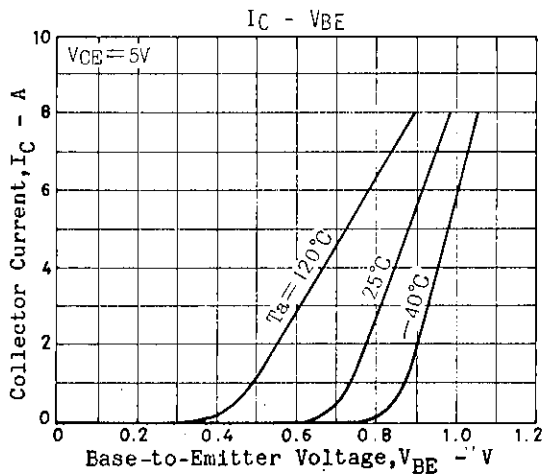
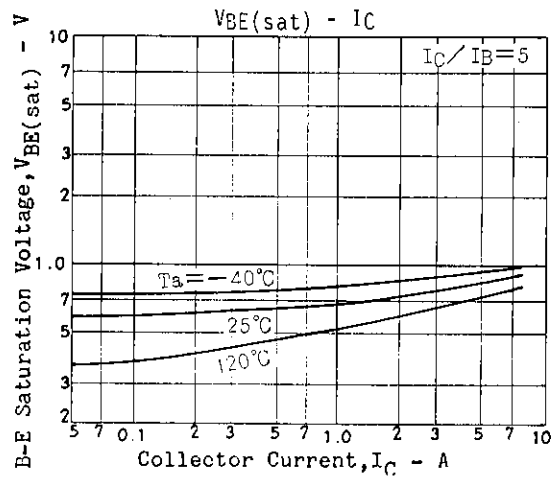
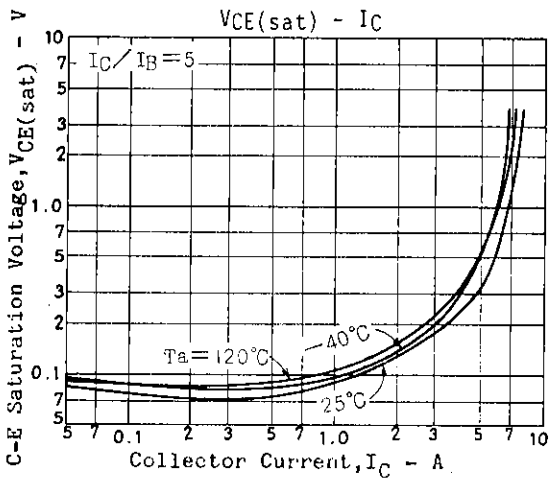
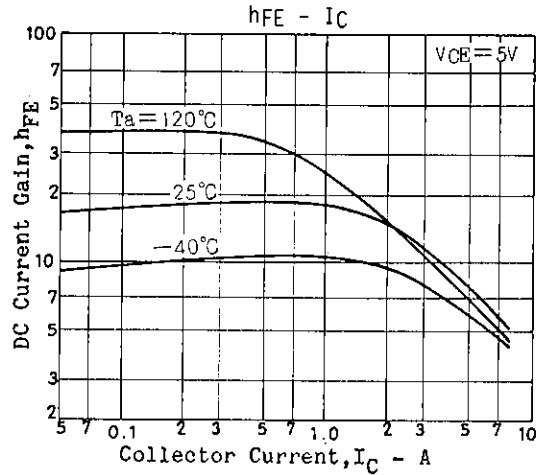
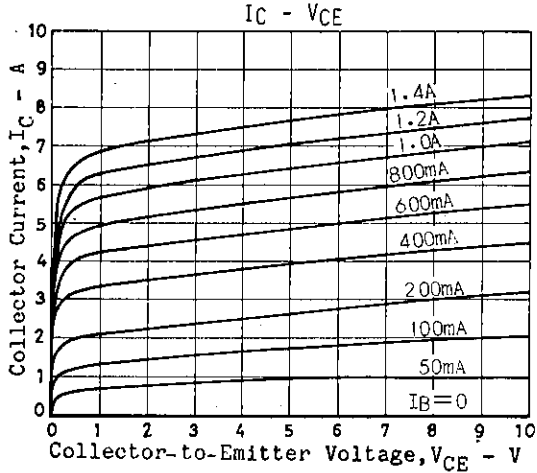
**Switching Time Test Circuit**

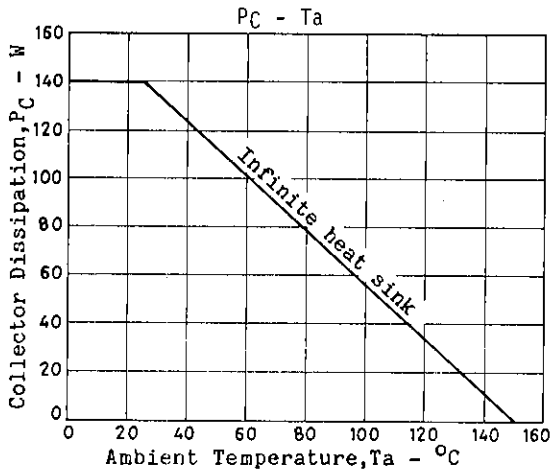
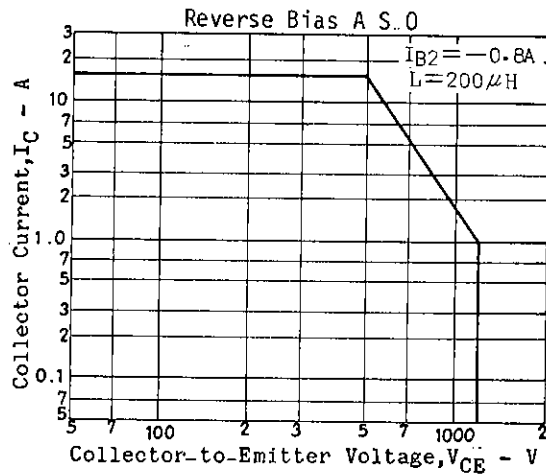
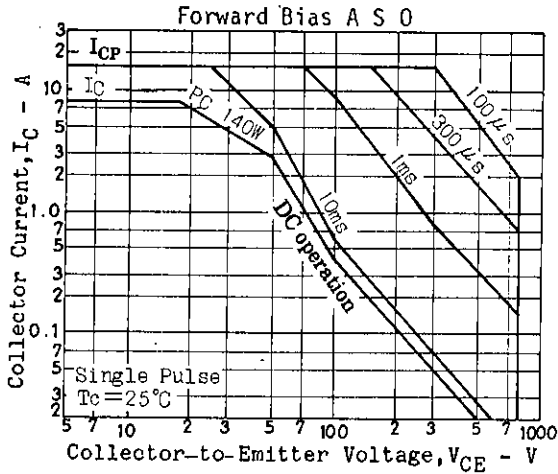


**Package Dimensions 2022**  
(unit: mm)



**SANYO Electric Co., Ltd. Semiconductor Business Headquarters**  
 TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN





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